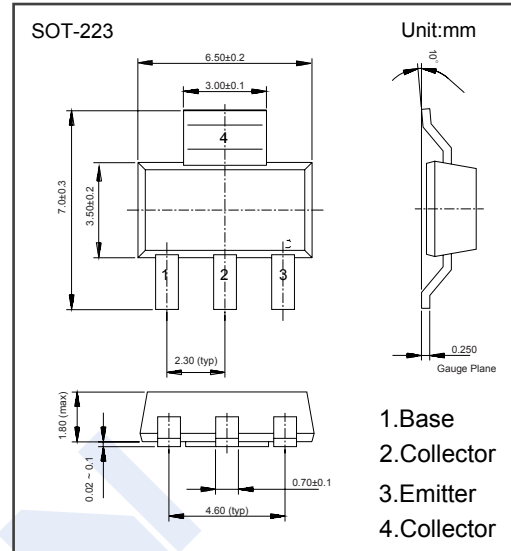


PNP Transistors

PZT2907A (KZT2907A)

■ Features

- Epitaxial planar die construction
- Complementary to PZT2222A



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-60	V
Collector - Emitter Voltage	V_{CE0}	-60	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to 150	

PNP Transistors

PZT2907A (KZT2907A)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _c = -100 μA, I _E = 0	-60			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -10 mA, I _B = 0	-60			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _c = 0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _c =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-150 mA, I _B =-15mA			-0.4	V
		I _c = -500 mA, I _B = -50mA			-1.6	
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-150 mA, I _B =-15mA			-1.3	
		I _c = -500 mA, I _B = -50mA			-2.6	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _c =- 0.1mA	75			
	h _{FE(2)}	V _{CE} = -10V, I _c = -1mA	100			
	h _{FE(3)}	V _{CE} = -10V, I _c =- 10mA	100			
	h _{FE(4)}	V _{CE} = -10V, I _c = -150mA	100		300	
	h _{FE(5)}	V _{CE} = -10V, I _c = -500mA	50			
Delay time	t _d	I _c =-150mA, I _{B1} =I _{B2} =-15mA			12	nS
Rise time	t _r				30	
Storage time	t _s				300	
Fall time	t _f				65	
Emitter input capacitance	C _{ib}	V _{EB} = -2V, I _c = 0, f=1MHz			30	pF
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz			8	
Transition frequency	f _T	V _{CE} = -20V, I _c = -50mA, f=100MHz	200			MHz